## 1. General description

NPN high-voltage low  $V_{CEsat}$  transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9215Z-Q

#### 2. Features and benefits

- · High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- Medium power SMD plastic package
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- · LED driver for LED chain module
- LCD backlighting
- · Automotive motor management
- Switch Mode Power Supply (SMPS)

#### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	150	V
I <sub>C</sub>	collector current		-	-	2	Α
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 10 V; $I_{C}$ = 100 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	100	240	-	



# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	C; C
2	С	collector		в
3	E	emitter		B — —
4	С	collector	1 2 3	Ė
			SC-73 (SOT223)	sym016

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package	Package						
	Name	Description	Version					
PBHV8215Z-Q		plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	<u>SOT223</u>					

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBHV8215Z-Q	V8215Z

2/12

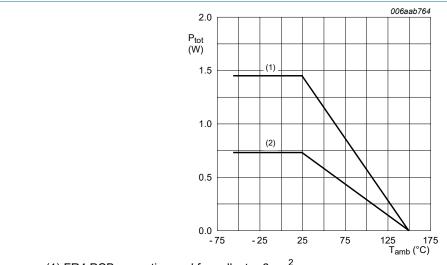
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	350	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	150	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	2	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	4	Α
I <sub>BM</sub>	peak base current	-		-	500	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.45	W
			[2]	-	0.73	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm $^2$ . Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



- (1) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (2) FR4 PCB, standard footprint

**Power derating curves** 

**Product data sheet** 

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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	-	85	K/W
junction to am	junction to ambient		[2]	-	-	170	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

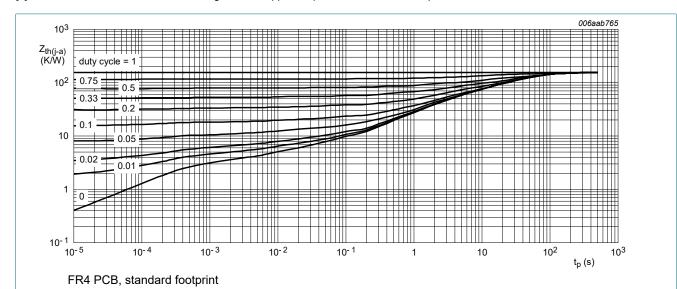
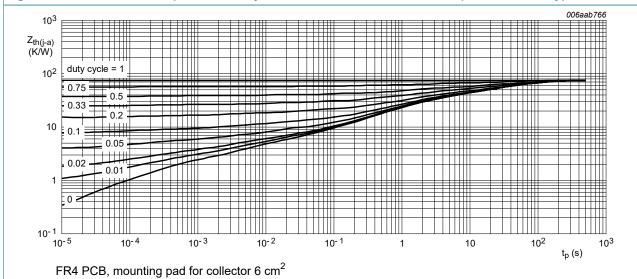


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

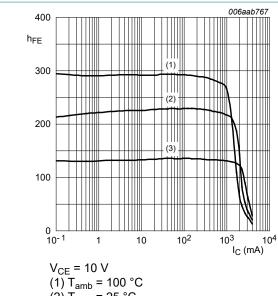


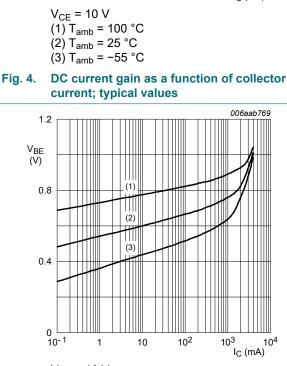
## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 120 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 120 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	10	μΑ
I <sub>ЕВО</sub>	emitter-base cut-off current	V <sub>EB</sub> = 4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
CES	collector-emitter cut-off current	V <sub>CE</sub> = 120 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 10 V; $I_{C}$ = 100 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	100	240	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	100	230	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 1.5 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	90	210	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 2 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	55	130	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = 100 mA; $I_B$ = 20 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	15	30	mV
		$I_C$ = 1 A; $I_B$ = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	90	170	mV
		$I_C$ = 1.5 A; $I_B$ = 300 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	130	220	mV
		$I_C = 2 \text{ A}$ ; $I_B = 400 \text{ mA}$ ; pulsed; $t_p \le$	-	170	280	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	85	140	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage		-	1	1.2	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 6 V; I <sub>C</sub> = 0.5 A; I <sub>Bon</sub> = 0.1 A;	-	20	-	ns
r	rise time	I <sub>Boff</sub> = -0.1 A; T <sub>amb</sub> = 25 °C	-	280	-	ns
on	turn-on time		-	300	-	ns
·s	storage time		-	2165	-	ns
t <sub>f</sub>	fall time		-	275	-	ns
off	turn-off time		-	2440	-	ns
fт	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	33	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 20 V; $I_{E}$ = 10 mA; $I_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C	-	17	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = 0 \text{ A}; i_c = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-	500	-	pF

**Product data sheet** 





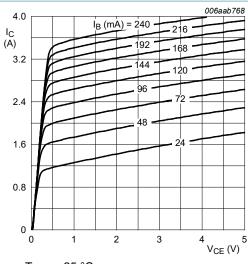
 $V_{CE}$  = 10 V

(1)  $T_{amb} = -55$  °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

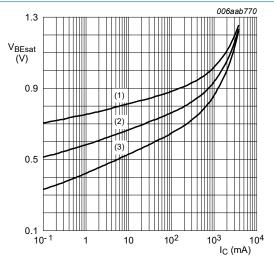
(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 6. Base-emitter voltage as a function of collector current; typical values



 $T_{amb}$  = 25 °C

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 $I_C/I_B = 5$ 

(1)  $T_{amb} = -55$  °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

6/12

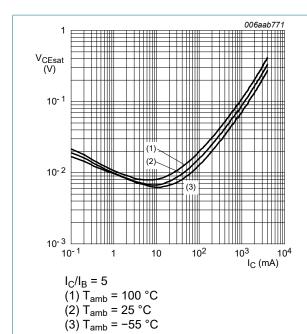


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

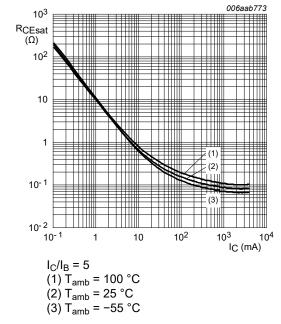


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

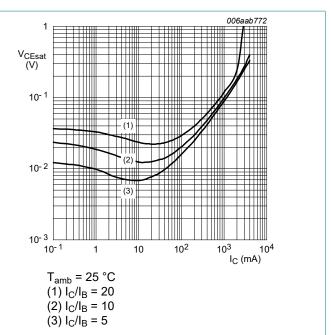


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

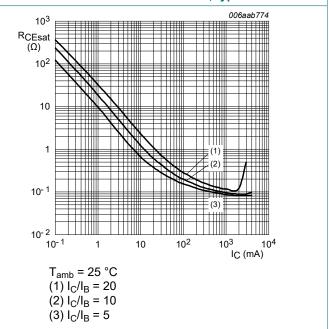
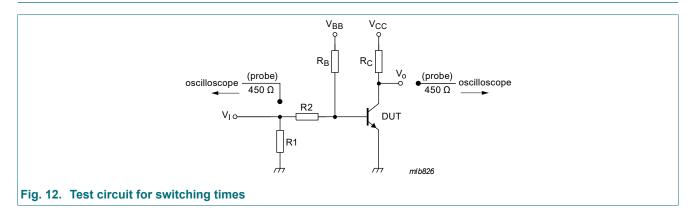


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

### 150 V, 2 A NPN high-voltage low VCEsat transistor

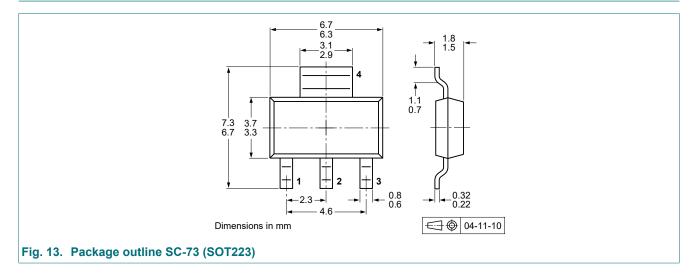
## 11. Test information



### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

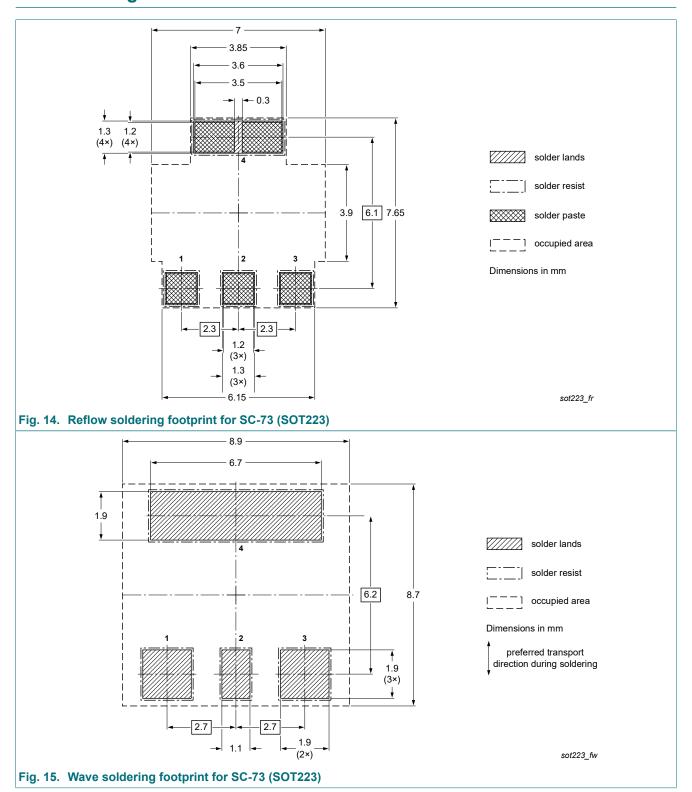
# 12. Package outline



**Product data sheet** 

#### 150 V, 2 A NPN high-voltage low VCEsat transistor

# 13. Soldering



150 V, 2 A NPN high-voltage low VCEsat transistor

# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8215Z-Q v.1	20230712	Product data sheet	-	-

### 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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### 150 V, 2 A NPN high-voltage low VCEsat transistor

## **Contents**

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	4
10.	. Characteristics	5
11.	Test information	8
12.	Package outline	8
13.	. Soldering	9
14.	Revision history	.10
15.	Legal information	.11

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